

### **INCHANGE SEMICONDUCTOR**

# isc N-Channel MOSFET Transistor

## 2SK856

### DESCRIPTION

- Drain Current –I\_D=45A@ T\_C=25 $^\circ\!\mathrm{C}$
- Drain Source Voltage-: V<sub>DSS</sub>=60V(Min)
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### APPLICATIONS

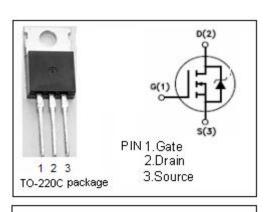
• Designed for use in switch mode power supplies and general purpose applications.

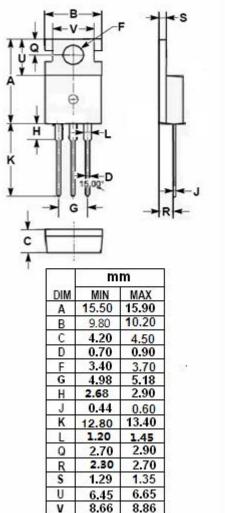
#### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

| SYMBOL           | ARAMETER                                  | VALUE   | UNIT |
|------------------|---|---------|------|
| V <sub>DSS</sub> | Drain-Source Voltage (V <sub>GS</sub> =0) | 60      | V    |
| $V_{GS}$         | Gate-Source Voltage                       | ±20     | V    |
| ID               | Drain Current-continuous@ TC=25°C         | 45      | А    |
| P <sub>tot</sub> | Total Dissipation@TC=25℃                  | 125     | W    |
| Tj               | Max. Operating Junction Temperature       | 150     | °C   |
| T <sub>stg</sub> | Storage Temperature Range                 | -55~150 | °C   |

#### THERMAL CHARACTERISTICS

| SYMBOL              | PARAMETER                               | МАХ  | UNIT |
|---------------------|---|------|------|
| R <sub>th j-c</sub> | Thermal Resistance, Junction to Case    | 1.67 | °C/W |
| R <sub>th j-a</sub> | Thermal Resistance, Junction to Ambient | 62.5 | °C/W |





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| SYMBOL               | PARAMETER                        | CONDITIONS                                 | MIN | TYP. | МАХ  | UNIT |  |  |  |
|----------------------|----------------------------------|--|-----|------|------|------|--|--|--|
| V <sub>(BR)DSS</sub> | Drain-Source Breakdown Voltage   | V <sub>GS</sub> =0; I <sub>D</sub> = 10mA  | 60  |      |      | V    |  |  |  |
| V <sub>GS(TH)</sub>  | Gate Threshold Voltage           | V <sub>DS</sub> =0; I <sub>D</sub> = 1mA   | 1.5 |      | 3.5  | V    |  |  |  |
| R <sub>DS(ON)</sub>  | Drain-Source On-stage Resistance | V <sub>GS</sub> = 10V; I <sub>D</sub> =25A |     |      | 0.03 | Ω    |  |  |  |
| I <sub>GSS</sub>     | Gate Source Leakage Current      | V <sub>GS</sub> = ±16V; V <sub>DS</sub> =0 |     |      | ±100 | nA   |  |  |  |
| IDSS                 | Zero Gate Voltage Drain Current  | V <sub>DS</sub> =60V; V <sub>GS</sub> = 0  |     |      | 0.1  | mA   |  |  |  |

### • ELECTRICAL CHARACTERISTICS (Tc=25°C)

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